

TOSHIBA Transistor Silicon NPN Epitaxial Type

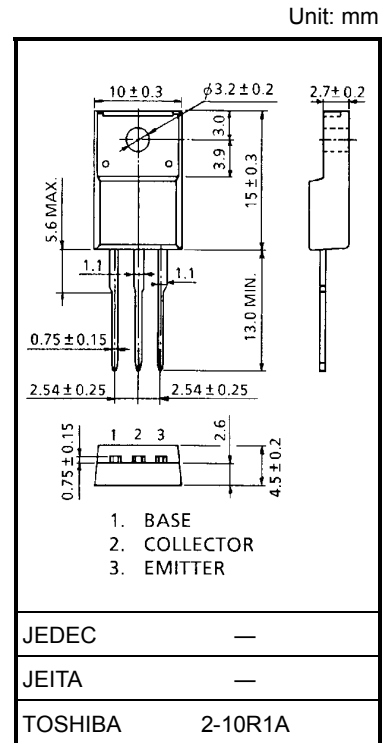
2SC4793

Power Amplifier Applications
 Driver Stage Amplifier Applications

- High transition frequency: $f_T = 100 \text{ MHz (typ.)}$
- Complementary to 2SA1837

Maximum Ratings ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	230	V
Collector-emitter voltage	V_{CEO}	230	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	1	A
Base current	I_B	0.1	A
Collector power dissipation	P_C	$T_a = 25^\circ\text{C}$	2.0
		$T_c = 25^\circ\text{C}$	20
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

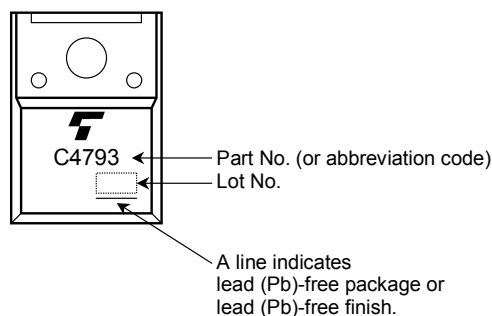


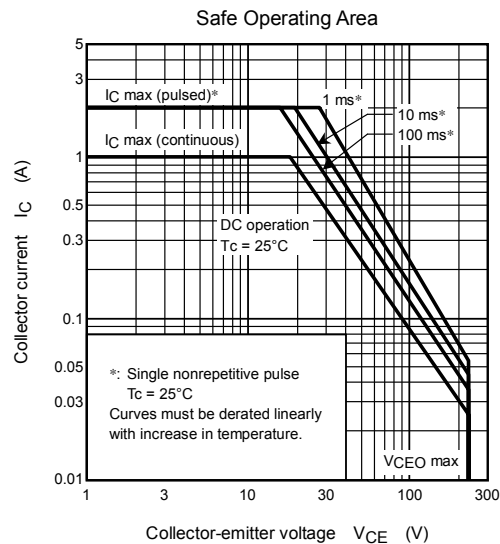
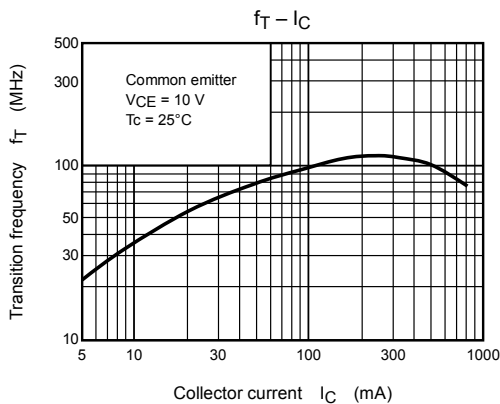
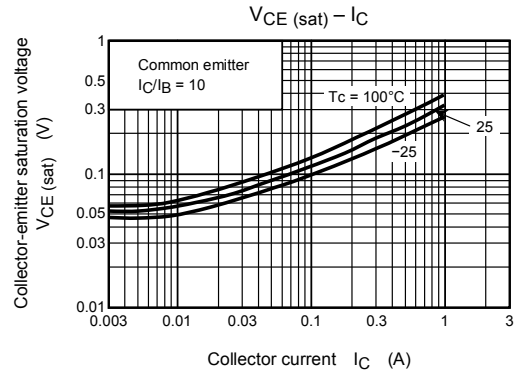
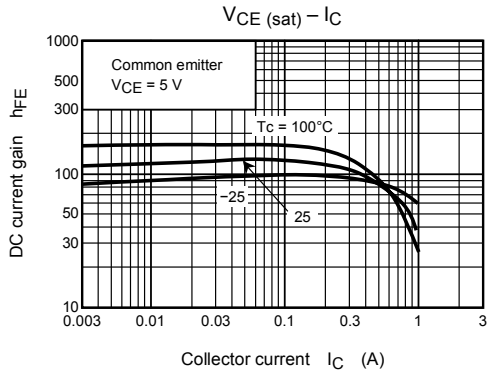
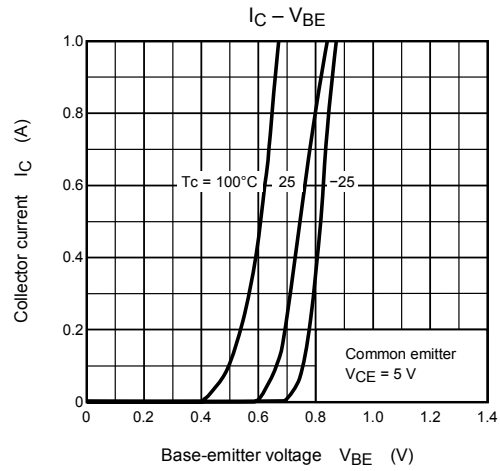
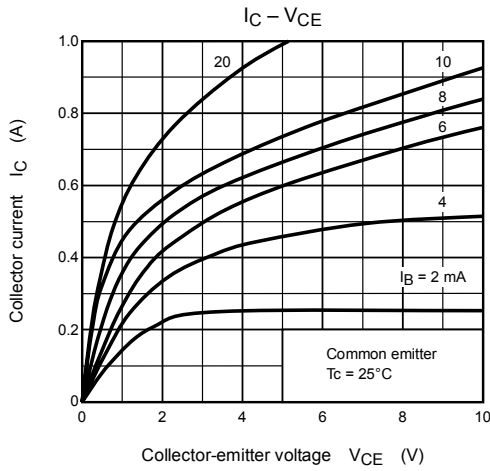
Weight: 1.7 g (typ.)

Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 230 \text{ V}, I_E = 0$	—	—	1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$	—	—	1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	230	—	—	V
DC current gain	h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 100 \text{ mA}$	100	—	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	—	—	1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 5 \text{ V}, I_C = 500 \text{ mA}$	—	—	1.0	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 100 \text{ mA}$	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	20	—	pF

Marking





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